

BC856BS 65 V, 100 mA PNP/PNP general-purpose transistor Rev. 01 — 11 August 2009 Produ

Product data sheet

1. Product profile

1.1 General description

PNP/PNP general-purpose transistor pair in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number			NPN/NPN	NPN/PNP
	NXP	JEITA	complement	complement
BC856BS	SOT363	SC-88	BC846BS	BC846BPN

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- AEC-Q101 qualified

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V_{CEO}	collector-emitter voltage	open base	-	-	-65	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	$V_{CE} = -5 V;$ $I_C = -2 mA$	200	290	450	



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2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		1 2 3
			sym018

3. Ordering information

Table 4. Ordering information				
Type number	Package			
	Name	Description	Version	
BC856BS	SC-88	plastic surface-mounted package; 6 leads	SOT363	

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
BC856BS	*E6

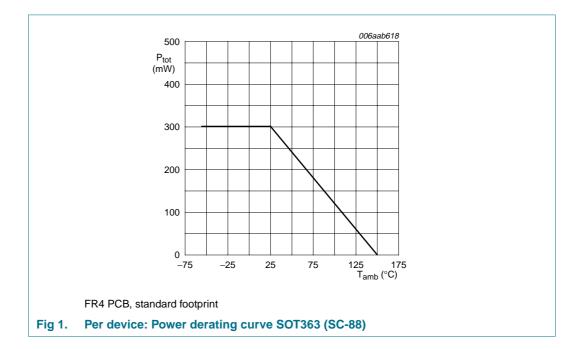
- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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5. Limiting values

Table 6. In accorda	Limiting values nce with the Absolute Maxim	um Rating System (I	IEC 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
Per transi	stor				
V _{CBO}	collector-base voltage	open emitter	-	-80	V
V _{CEO}	collector-emitter voltage	open base	-	-65	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-200	mA
I _{BM}	peak base current	single pulse; $t_p \leq 1 ms$	-	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	200	mW
Per devic	e				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	300	mW
Тj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

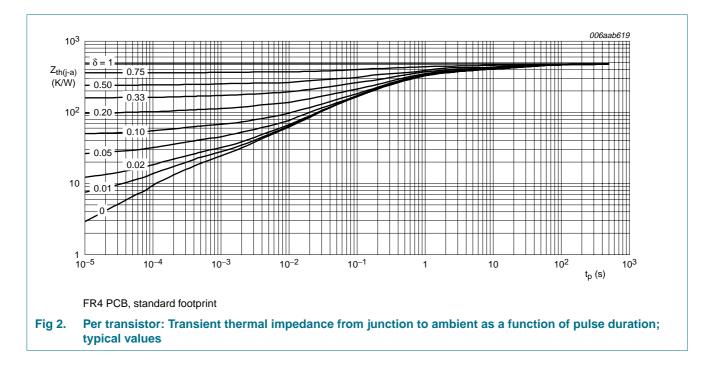


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6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	625	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	230	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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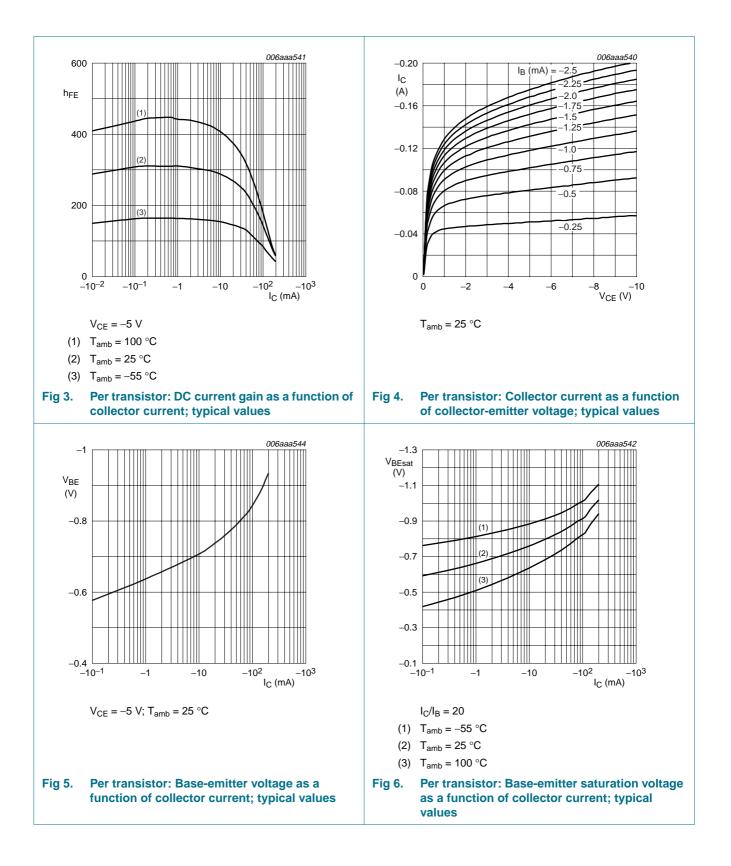
7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I _{CBO}	collector-base cut-off	$V_{CB} = -50$ V; $I_E = 0$ A	-	-	-15	nA
	current	$\label{eq:VCB} \begin{array}{l} V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \\ T_{j} = 150 \ ^{\circ}\text{C} \end{array}$	-	-	-5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -6 V; I_C = 0 A$	-	-	-100	nA
h _{FE} DC current gain		$V_{CE} = -5 V$				
		I _C = -10 μA	-	270	-	
		$I_{\rm C} = -2 \rm{mA}$	200	290	450	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-55	-100	mV
	$I_{C} = -100 \text{ mA}; I_{B} = -5 \text{ mA}$	-	-200	-300	mV	
V _{BEsat}	r _{BEsat} base-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-755	-850	mV
		$I_{\rm C} = -100 \text{ mA}; I_{\rm B} = -5 \text{ mA}$	-	-900	-	mV
V _{BE}	base-emitter voltage	$V_{CE} = -5 V$				
		$I_{\rm C} = -2 \rm{mA}$	-600	-650	-750	mV
		$I_{\rm C} = -10 \text{ mA}$	-	-	-820	mV
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	2.3	-	pF
C _e	emitter capacitance	$V_{EB} = -0.5 V;$ $I_{C} = i_{c} = 0 A; f = 1 MHz$	-	10	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	100	-	-	MHz
NF	noise figure		-	1.6	-	dB
		$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega; \text{ f} = 1 \text{ kHz};$ B = 200 Hz	-	2.9	-	dB

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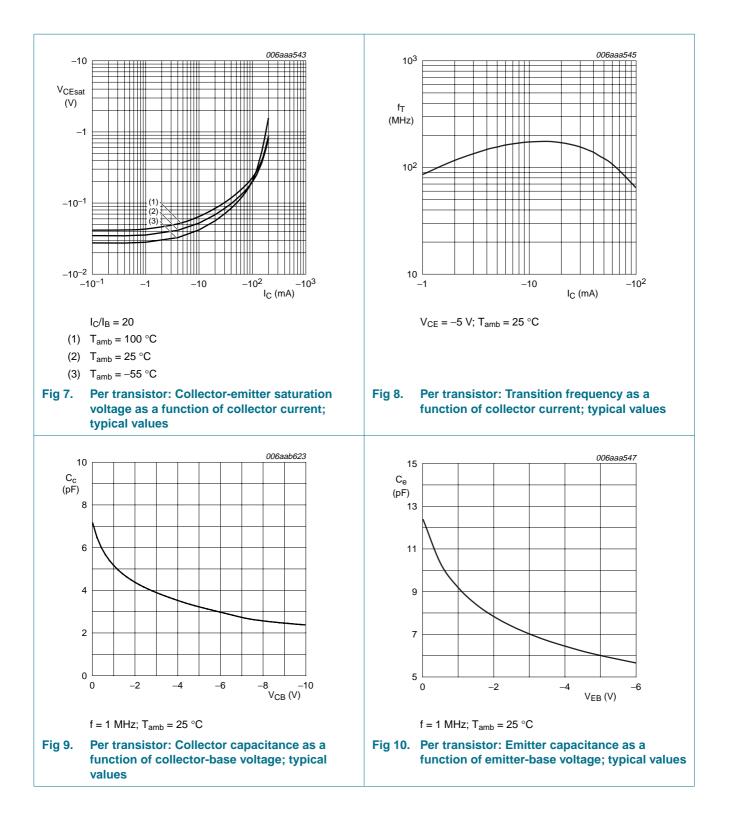
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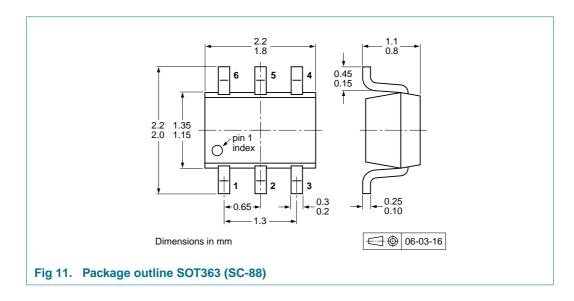
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8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing	g quantity
				3000	10000
BC856BS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

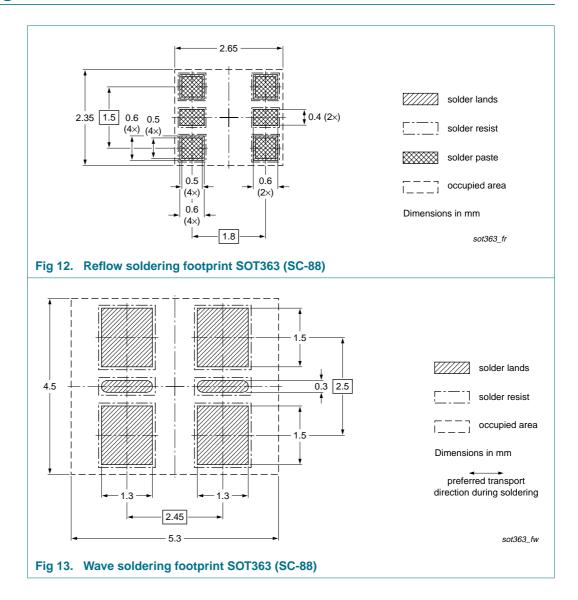
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

[2] T1: normal taping

[3] T2: reverse taping

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11. Soldering



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12. Revision history

Table 10. Revision his	Ible 10. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BC856BS_1	20090811	Product data sheet	-	-	

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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